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Application Number	09/977,069
Filing Date	October 11, 2001
First Named Inventor	Ramanath, G.
Art Unit	2811
Examiner Name	To Be Assigned
Attorney Docket Number	020752-000121US

U.S. PATENT DOCUMENTS

Examiner	Cite No. ¹	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
EK	A	Ahrens, C. et al., "Electrical characterization of conductive and non-conductive barrier layers for Cu-metallization," Applied Surface Science, 1995, pp. 285-290, Vol. 91.	
EK	B	Ding, P.J. et al., "Effects of the addition of small amounts of Al to copper: Corrosion, resistivity, adhesion, morphology, and diffusion," J. Appl. Phys., April 1994, pp. 3627-3631, Vol. 75(7).	
EK	C	Ding, P.J. et al., "Oxidation resistant high conductivity copper films," Appl. Phys. Lett. May 1994, pp. 2897-2899, Vol. 64(21).	
EK	D	McBrayer, J.D. et al., "Diffusion of metals in silicon dioxide," J. Electrochem. Soc., June 1986, pp. 1242-1246, Vol. 133(6).	
	E	Moshfegh, A.Z. et al., "Bias sputtered Ta modified diffusion barrier in Cu/Ta(Vb)/Si(111) structures," Thin Solid Films, 2000, pp. 10-17, Vol. 370.	
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	G	Reed, M.A. and TOUR, J.M., "Computing with molecules," Scientific American, 2000, pp. 86-93, Vol. 282(6).	
	H	Gekiguchi, A. et al., "Microstructural and morphological changes during thermal cycling of Cu thin films," J. Japan Inst. Metals, 2000, pp. 379-382, Vol. 64(5).	

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